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(54) Title: METHOD FOR GROWING BETA PHASE OF GALLIUM OXIDE (β -Ga₂O₃) SINGLE CRYSTALS FROM THE MELT CONTAINED WITHIN A METAL CRUCIBLE

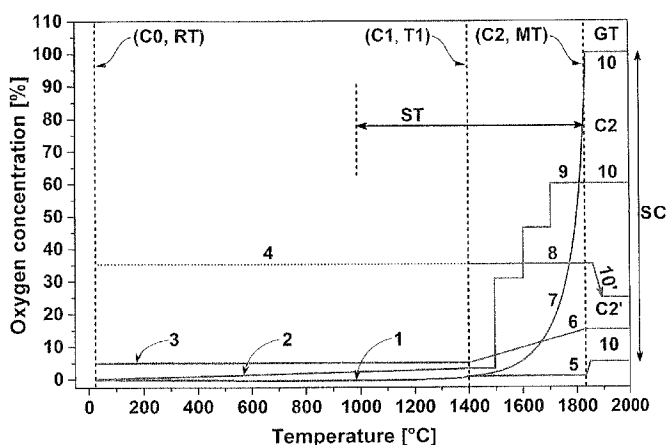


Fig. 2A

(57) Abstract: A method for growing beta phase of gallium oxide (β -Ga₂O₃) single crystals from the melt contained within a metal crucible surrounded by a thermal insulation and heated by a heater. A growth atmosphere provided into a growth furnace has a variable oxygen concentration or partial pressure in such a way that the oxygen concentration reaches a growth oxygen concentration value (C2, C2', C2'') in the concentration range (SC) of 5 - 100 vol. % below the melting temperature (MT) of Ga₂O₃ or at the melting temperature (MT) or after complete melting of the Ga₂O₃ starting material adapted to minimize creation of metallic gallium amount and thus eutectic formation with the metal crucible. During the crystal growth step of the β -Ga₂O₃ single crystal from the melt at the growth temperature (GT) the growth oxygen concentration value (C2, C2', C2'') is maintained within the oxygen concentration range (SC).

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Method for growing beta phase of gallium oxide (β -Ga₂O₃) single crystals from the melt contained within a metal crucible

Description

TECHNICAL FIELD

The present invention relates in general to a method for growing oxide single crystals from the melt contained within a metal crucible and in particular for growing beta phase of gallium oxide (β -Ga₂O₃) single crystals from the melt contained within the metal crucible.

BACKGROUND OF THE INVENTION

Beta phase of gallium oxide (β -Ga₂O₃) belongs to the group of transparent semiconducting oxides. It is a semiconductor with a wide optical bandgap of 4.8 eV, what makes it transparent in the visible down to deep ultraviolet spectrum (DUV). Such unique properties offer opportunities for developing a number of applications in the field of electronics (e.g. field effect transistors) and optoelectronics (e.g. light emitting diodes), and environmental monitoring (e.g. gas sensors). For most of such applications bulk single crystals are required, from which electronic or optoelectronic components or substrates for thin film depositions could be prepared.

For industrial applications large single crystals of high quality are demanded. In the case of oxide single crystals they are typically grown from the melt contained within a metal crucible, e.g. comprising platinum for low and moderate melting points (below 1500°C), iridium for high melting points (roughly between 1500-2200°C) and molybdenum, tungsten or rhenium for very high melting point oxides (above 2200°C). There are several crystal growth techniques operating with the use of the metal crucible, including the Czochralski method, Kyropoulos method, Vertical or Horizontal Bridgman method, Vertical Gradient Freeze method, shaped crystal growth methods, such as the Stepanov, Noncapillary Shaping (NCS) and Edge-Defined Film-Fed Growth (EFG) methods and Levitation Assisted Self-Seeding Crystal Growth method (LASSCGM).

Gallium oxide is thermodynamically unstable at high temperatures, what in combination with high melting point (about 1820°C) leads to a strong decomposition. To stabilize this compound high oxygen partial pressure (or concentration) is required. However, this creates additional difficulties since iridium or iridium alloy crucible must be used, which has a tendency to a strong oxidation at low and moderate temperatures in particular, although small oxygen

concentration can be used (typically maximum 2%). Other metal crucibles cannot withstand even very small oxygen concentrations, while platinum has too low melting point to be used for gallium oxide.

High oxygen concentration for growing β -Ga₂O₃ single crystals can be applied for those growth methods, which operate on a crucible-free basis. An example of such method applied for β -Ga₂O₃ single crystals is the Optical Floating Zone (OFZ) method, e.g. as described in the publications by Ueda et al., Appl. Phys. Lett. 70 (1997) 3561, Appl. Phys. Lett. 71 (1997) 933, Tomm et al., Sol. Cells 66 (2001) 369, Villora et al., J. Cryst. Growth 270 (2004) 420, Appl. Phys. Lett. 92 (2008) 202120 and US patent document No. US 8,747,553 B2. In this method a very small portion of the Ga₂O₃ feed rod is molten by a light beam focused on a tip of the feed rod. The molten portion of the feed rod is contacted with a seed, on which a crystal is grown during translation of the seed with respect to the light beam. Due to a very small molten area of the feed rod (very small cross section area of the light beam) the resulted crystal diameter is also small, typically not exceeding 5-6 mm. Although larger crystal (about 25 mm in diameter) was demonstrated, this seems to be a limit for the crystal size, whose quality is highly deteriorated due inhomogeneity of temperature gradients across the liquid-solid growth interface as the result of very small cross section area of the light beam with respect to a cross section of the growth interface. So far, the OFZ method has not found any industrial applications for oxide crystals, due to too small crystal volume.

Another crucible-less method applied to β -Ga₂O₃ crystals is the Verneuil method described by Chase, J. Am. Ceram. Soc. 47 (1964) 470. Here, the powdered starting material of Ga₂O₃ is molten with H₂-O₂ flames and the liquid drops fall down on a seed and solidify to form a crystal. Due to poor structural quality and small crystal size, this method has not found continuation in the research of β -Ga₂O₃ growth.

β -Ga₂O₃ single crystals were already grown from melt contained in an iridium crucible with the use of the Czochralski method as described in the publications by Tomm et al., J. Cryst. Growth 220 (2000) 510 and Galazka et al., Cryst. Res. Technol. 45 (2010) 1229 and Galazka et al. J. Cryst. Growth 404 (2014) 184. In the Czochralski method the crystal is pulled out directly from an exposed melt surface contained within the iridium crucible. In both cases a dynamic self-adjusting growth atmosphere containing CO₂ was used. CO₂ decomposes with temperature and releases more oxygen as temperature increases. In this way about 1.2 vol. % of oxygen can be provided at melting point of Ga₂O₃ with no harm to the iridium crucible, because at low and moderate temperatures, where iridium oxidizes the most, oxygen concentration is kept at a very

low level. Yet more oxygen (up to 4 %) was provided by applying an overpressure of CO₂ at the level of several bar. The oxygen concentration provided by CO₂ is sufficient to grow cylindrical β-Ga₂O₃ single crystals with diameter of about 20-22 mm from the iridium crucible of 40 mm in diameter.

Another method applied to grow β-Ga₂O₃ single crystals from the melt contained in an iridium crucible is the EFG method, as described in the publication to Aida et al., Jpn. J. Appl. Phys. 47 (2008) 8506 and patent application documents JP 2013082587 A, JP 2013103863 A, JP 2013124216 A, JP 2013227160 A, JP 2013237591 A, JP 2013241316 A, WO 2013073497 A1 and WO 2014073314A1. In this method an iridium die is provided in the iridium crucible, which has small openings and a slit on the top that communicates with the openings. The melt is transported through the die by capillary forces to the top slit, from which a crystal sheet is pulled out from the die. The melt surface area and the melt volume in the die slit are typically small, therefore small oxygen concentration is likely sufficient for the stable crystal growth, although these documents do not refer to any oxygen concentration when using iridium components. The crystal sheets may have a relatively large longitudinal cross-section, but typically small thickness (such as a few millimeters) what limits the total crystal volume being a crucial aspect for industrial applications.

To grow larger crystals, such as over 1 kg by weight (e.g. 2 inch in diameter and 4-5 inch long in the case of the Czochralski method), large crucibles must be used. This means much larger exposed melt surface which is in a direct contact with a growth atmosphere providing oxygen, much larger crystal volume in which oxygen from the growth atmosphere must be distributed and much larger contact surface area between the liquid Ga₂O₃ and iridium crucible. Decomposition of Ga₂O₃ produces different species in the gas phase leading to a strong evaporation, but also metallic gallium in the liquid phase (due to oxygen loss). Such liquid metallic gallium is created at the melt surface and in the melt bulk, and changes the melt stoichiometry and temperature, therefore growing a crystal from such affected melt surface is practically impossible. Even if the beginning of the growth is successful, metallic gallium forms a film on the crystal surface, which blocks heat transfer through the growing crystal, what in turn induces growth instabilities decreasing a usable crystal volume. Metallic gallium particles that attach to the crystal surface and built in the crystal lattice significantly deteriorates the crystal quality, which may not be usable for most of the applications. Moreover, metallic gallium transported within the melt via convection flows reacts with solid iridium crucible (and the die in the case of the case of the shaped techniques) and form eutectic leading to a severe crucible

damage and consequently high economical losses. Eutectic formation highly increases with increasing the melt volume and crucible size. These negative effects limit the growth of large β - Ga_2O_3 single crystals in terms of a reasonable volume, crystal quality, growth stability and iridium crucible life time, which all define the production yield and costs.

SUMMARY OF THE INVENTION

An object of the present invention is to provide conditions for growing β - Ga_2O_3 single crystals from the melt, which minimize Ga_2O_3 decomposition and eliminate a damage of a metal crucible as the result of metallic gallium formation forming eutectic with iridium.

Another object of the present invention is to provide conditions for growing β - Ga_2O_3 single crystals from the melt, which ensure a stable crystal growth process.

Yet another object of the present invention is to provide high quality β - Ga_2O_3 single crystals, which would meet requirements for electronic and optoelectronic applications, including substrates for epitaxy.

Still another object of the present invention is to provide conditions for growing β - Ga_2O_3 single crystals from the melt by different growth techniques utilizing a metal crucible.

Further object of the present invention is to provide a method for growing β - Ga_2O_3 single crystals from the melt contained within a metal crucible, which would enable for obtaining large crystals of at least 0.5 kg, in particular much over 1 kg.

In a more general aspect, a yet further object of the present invention is to provide a method for growing other oxide compounds, which are thermally unstable at high temperatures, in particular other transparent semiconducting oxides, such as, but not limited to ZnO , In_2O_3 , NiO , SnO_2 , BaSnO_3 and like.

According to the first aspect of the invention a method for growing beta phase of gallium oxide (β - Ga_2O_3) single crystals from the melt contained within a metal crucible is provided, which comprises the steps of:

- providing into a growth chamber a thermal system or growth furnace comprising the metal crucible containing the Ga_2O_3 starting material, a thermal insulation surrounding the metal crucible and a heater disposed around the metal crucible;
- providing or creating a crystal seed within the growth furnace;
- introducing at least into the growth furnace a growth atmosphere containing oxygen;
- heating up the metal crucible by the heater, which in turns heats up the Ga_2O_3 starting material until melting;

- contacting the crystal seed with the molten Ga₂O₃ starting material contained within the metal crucible;
- growing a β-Ga₂O₃ single crystal on the crystal seed by temperature gradients between the crystal seed and the melt;
- cooling down the grown β-Ga₂O₃ single crystal to room temperature once the crystal growth step has been completed;

wherein the method further comprises the step of

- i) providing into the growth furnace the growth atmosphere with a variable oxygen concentration or partial pressure in such a way that the oxygen concentration reaches a growth oxygen concentration value in the concentration range of 5 – 100 vol. % below the melting temperature of Ga₂O₃ or at the melting temperature or after complete melting of the Ga₂O₃ starting material adapted to minimize creation of metallic gallium amount and thus eutectic formation with the metal crucible and to improve stoichiometry of the Ga₂O₃ starting material and crystal growth stability; and
- ii) maintaining the growth oxygen concentration value within the oxygen concentration range during the crystal growth step of the β-Ga₂O₃ single crystal from the melt at the growth temperature.

In a preferred embodiment of the present invention the oxygen concentration:

- iii) does not exceed an intermediate oxygen concentration value in the range of 0 - 5 vol. % during the heating up step from room temperature to an intermediate temperature value, intermediate temperature value being located within the temperature range between 1000 °C and the melting temperature of Ga₂O₃;
- iv) increases from the intermediate oxygen concentration value to the growth oxygen concentration value in the concentration range of 5 – 100 vol. % during the heating up step from the intermediate temperature value to the melting temperature of Ga₂O₃ or at the melting temperature or after complete melting of the Ga₂O₃ starting material if the intermediate temperature value substantially equals to the melting temperature.

Advantageously, the oxygen concentration:

- v) decreases from the growth oxygen concentration value to a final oxygen concentration value being lower than the growth oxygen concentration value during the cooling down step from the growth temperature to room temperature.

Preferably the growth oxygen concentration value is substantially constant within the oxygen concentration range at the growth temperature during the entire crystal growth step.

Alternatively, the growth oxygen concentration value decreases to a second oxygen growth concentration value within the oxygen concentration range at the growth temperature after an early stage of the crystal growth step. In further alternative embodiment, the growth oxygen concentration value increases to a third growth oxygen concentration value within the oxygen concentration range at the growth temperature at the later stage of the crystal growth step. In still alternative embodiment, the growth oxygen concentration value first decreases to a second growth oxygen concentration value within the oxygen concentration range at the growth temperature after an early stage of the crystal growth step, and increases to a third growth oxygen concentration value within the oxygen concentration range at the growth temperature at the later stage of the crystal growth step.

In a preferred embodiment of the present invention, the growth atmosphere contains in addition to oxygen at least one of the gases selected from the group consisting of Ar, N₂, He, Ne, CO₂, CO, H₂ and H₂O, or any combination thereof.

Advantageously, the growth atmosphere can be applied to the Czochralski method, Kyropoulos method, Vertical Bridgman method, Vertical Gradient Freeze method, Horizontal Bridgman method, to shaped crystal growth techniques, such as Stepanov, Noncapillary Shaping and Edge-Defined Film-Fed Growth methods, Levitation Assisted Self-Seeding Crystal Growth method and Micro-Pulling Down method.

According to the second aspect of the invention a bulk β -Ga₂O₃ single crystal is provided, which is obtained by the above-describe method.

According to the third aspect of the present invention a use of bulk β -Ga₂O₃ single crystal is provided, which is in the form of fabricated wafers or substrates for epitaxial films or layers.

The inventors have unexpectedly found out through a series of comprehensive experiments that a very high oxygen concentration can be used in connection with an iridium crucible or its alloys at high temperatures. This discovery is in a high contrast to a common, long-lasting believe being reflected in the literature and experiments, that oxygen concentration should not exceed about 2-5 vol. % in connection with iridium. An essential feature of the present method is to maintain a very high oxygen concentration during crystal growth (5 - 100 vol. %) from the melt contained within an iridium (or its alloy) crucible, while keeping lower oxygen concentration at lower temperatures during heating up / cooling down steps, when iridium oxidation rate is much higher as compared with high temperatures. Furthermore, partial pressure of iridium oxide at high temperatures is very high so that it simply evaporates and does not contaminate the melt inside the crucible, again, in contrast to high oxygen concentration

provided at low and moderate temperatures during heating up, when iridium oxide typically contaminates the melt. Moreover, with high oxygen concentration less oxygen vacancies, twins and grain boundaries are formed in a growing oxide crystal, therefore the crystal quality significantly improves. Most importantly, such growth conditions enable for obtaining large crystals (over 1 kg by weight) what is important from industrial point of view, and also extend life-time of iridium crucibles by elimination of eutectic formation between iridium and metallic gallium typically formed during decomposition process. Additionally, the teaching of the present invention has a general meaning and can be successfully applied to any high-melting point oxides requiring high oxygen partial pressure, including those thermo-chemically unstable ones.

More advantages and other features of the inventive method to growth bulk β -Ga₂O₃ single crystals or other thermally unstable oxide crystals will be apparent from the detailed description of the embodiments in reference to the drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1A and 1B are plots of amount of liquid metallic gallium and gaseous gallium suboxide (Ga₂O), respectively, produced during decomposition of Ga₂O₃ at its melting temperature;

Figs. 2A and 2B are plots of oxygen concentration in a growth atmosphere vs. temperature during heating up / growth and growth / cooling down steps, which demonstrate the principle of the present invention;

Fig. 3 schematically shows the principle of the Czochralski method to which the present invention can be applied;

Fig. 4 schematically shows the principle of the Kyropoulos method to which the present invention can be applied;

Figs. 5A and 5B schematically show the principle of the Vertical and Horizontal Bridgman method or Vertical Gradient Freeze method to which the present invention can be applied;

Fig. 6 schematically shows the principle of the shaped crystal growth methods to which the present invention can be applied; and

Fig. 7 schematically shows the principle of the Levitation Assisted Self-Seeding Crystal Growth method to which the present invention can be applied.

DETAILED DESCRIPTION OF THE EMBODIMENTS

Fig. 1A shows amount changes of liquid metallic gallium (Ga) in the Ga_2O_3 melt (that is at melting point of Ga_2O_3 which is 1820°C) as the result of Ga_2O_3 decomposition versus oxygen concentration interacting with the Ga_2O_3 melt. The metallic Ga amount **CR1** is formed within 2.3 mole of the Ga_2O_3 starting material contained within an iridium crucible of 50 mm in diameter and height to grow 1 inch diameter single crystal; the metallic Ga amount **CR2** is formed within 18 mole of the Ga_2O_3 starting material contained within an iridium crucible of 100 mm in diameter and height to grow 2 inch diameter single crystal, while the metallic Ga amount **CR3** is formed within 63 mole of the Ga_2O_3 starting material contained within an iridium crucible of 150 mm in diameter and height to grow 3 inch diameter single crystal. Metallic Ga forms with iridium (Ir) eutectic that destroys the crucible containing the Ga_2O_3 melt. In addition to liquid metallic Ga also gaseous metallic Ga is formed in the melt, which in areas adjacent to the crucible wall also forms Ga-Ir eutectic. Further, the presence of metallic Ga in the Ga_2O_3 melt creates difficulties in growing a $\beta\text{-Ga}_2\text{O}_3$ single crystal and/or obtaining good structural quality thereof, due to changes in melt chemistry and melting temperature. These negative effects, arising from metallic Ga, increases with a melt volume, as higher concentration of metallic Ga is produced. For example, in the case of a growth atmosphere containing 1 vol. % of oxygen the metallic Ga amount **CR2** increases with respect to **CR1** by factor of about 23, while the metallic Ga amount **CR3** increases with respect to **CR1** by factor of about 79. Other words, using 1 vol. % of oxygen growing 2 or 3 inch diameter single crystal will result in Ir crucible damage with no possibility to obtain a single crystal. The amount of metallic Ga can be significantly decreased, at least by several times, by increasing the oxygen concentration **OC** at the level of at least 5 vol. %. In the case of that lowermost value (5 vol. %) the metallic Ga amount **CR2** increases with respect to **CR1** by factor of only 8, while in the case of metallic Ga amount **CR3** - by factor of about 27. When considering a decrease of metallic Ga amount when using 5 vol. % of oxygen with respect to 1 vol. % of oxygen, it decreases by factor of 3 and 9 for **CR1** and **CR2**, **CR3**, respectively. As clearly shown in Fig. 1A, for higher oxygen concentrations in the range 5 - 100 vol. % the decrease of metallic Ga amount will be more pronounced. Plots **CR1**, **CR2** and **CR3** indicate that to minimize the metallic Ga amount a much higher oxygen concentration should be used with an increase of the crystal size to be grown.

Another essential finding of the present invention is that iridium oxide from oxidation of iridium at high temperatures does not contaminate the Ga_2O_3 melt and the growing crystal. This is due to a very high partial pressure of iridium oxide at high temperatures, which simply evaporate to the environment immediately after creation at the crucible wall.

In addition to metallic Ga, decomposition of the Ga_2O_3 melt produces a number of volatile species in the gas phase, including oxygen, Ga_2O , GaO and Ga, which evaporate to the environment. The most volatile species in addition to oxygen is Ga_2O , the amount versus oxygen concentration of which is shown in Fig. 1B. Applying oxygen concentration **OC** of at least 5 vol. % decreases amount (and fugacity) of Ga_2O by more than one order of magnitude, thus decreases the evaporation of Ga_2O_3 during the growth process. Minimizing of Ga_2O evaporation in addition to metallic Ga is crucial to keep the melt more stoichiometric and to stabilize the crystal growth process.

Therefore, by applying the oxygen concentration **OC** in the range between 5 – 100 vol. %, the Ga_2O_3 melt can be significantly stabilized by minimizing formation of metallic Ga in the Ga_2O_3 melt and Ga_2O vapor that evaporates from the melt surface. Thus it is sufficient for both crystal growth stability and iridium (or its alloy) crucible durability. It is to be stressed that such high oxygen concentrations (5 – 100 vol. %) in connection with the iridium crucible, which is suitable for growing Ga_2O_3 single crystals from the melt, has never been reported, mentioned or suggested in the prior art, despite of utilizing iridium crucibles for growing various oxide single crystals for decades.

The essence of the present invention is to apply a very high oxygen concentration (5 – 100 vol. %) for growing $\beta\text{-Ga}_2\text{O}_3$ single crystals from the melt contained within an iridium (or its alloy) crucible around the melting point of Ga_2O_3 which is 1820°C , while keeping a relatively low oxygen concentration at low and moderate temperatures, where iridium oxidizes the most and Ga_2O_3 decomposition is minor. This strategy is described in Fig. 2A during heating a crystal growth furnace up and growing a $\beta\text{-Ga}_2\text{O}_3$ single crystal, and in Fig. 2B during growing the $\beta\text{-Ga}_2\text{O}_3$ single crystal and cooling the crystal growth furnace down after the crystal growth process has been completed.

As shown in Fig. 2A, an initial oxygen concentration value **C0** is typically small at room temperature **RT**, usually in the range of 0 to about 3 vol. %. The oxygen concentration **OC** increases from the initial oxygen concentration value **C0** to an intermediate oxygen concentration value **C1** in the temperature range between room temperature **RT** and an intermediate temperature value **T1** in any way, e.g. linearly (profile 1), exponentially (profile 2), asymptotically, in a step-wise manner or in any combination thereof. Although the intermediate temperature value **T1** is 1400°C in this example it may have any value in the temperature range **ST** between 1000°C and the melting temperature **MT** of a Ga_2O_3 starting material. This exemplary value of 1400°C is a compromise between minimizing of the iridium crucible

oxidation (which may contaminate a Ga_2O_3 starting material) and avoiding Ga_2O_3 decomposition during the heating up step. Alternatively, in the temperature range between room temperature **RT** and the intermediate temperature value **T1** the oxygen concentration **OC** may be constant (i.e. **C0** = **C1**) as shown by profiles **3** and **4**. Although **C0** has typically a small value, in some applications it may have a very high value, such as 35 % (profile **4**). This is applicable to growth runs with fast heating rates (e.g. 300-500 K/h), when passing through temperatures critical for iridium is very fast. At higher temperatures, i.e. above **T1**, the Ga_2O_3 starting material is more susceptible to decomposition, while iridium oxidation decreases. Therefore the oxygen concentration can be increased to a higher value, i.e. a growth oxygen concentration value **C2** around the melting temperature **MT** of the Ga_2O_3 starting material, which is then maintained within an oxygen concentration range **SC** during the crystal growth step. In this transition region, the oxygen concentration **OC** can be increased in any way, as shown by different profiles **5** to **9** or any combination thereof. E.g. the oxygen concentration **OC** can be maintained at substantially low value of **C1** to the temperature near or at or just above the melting temperature **MT** and then it can be abruptly increased to the value **C2**, as shown by the profile **5**. Alternatively, the oxygen concentration **OC** can be maintained at a high constant value of **C1** in the temperature range **ST**, at the melting temperature **MT** and during the crystal growth step (**C2** = **C1**), as shown by the profile **8**. The oxygen concentration **OC** can be increased in the temperature range **ST** linearly (profile **6**), exponentially (profile **7**), in a step-wise manner (profile **9**), asymptotically or in any other manner. The way how the oxygen concentration increases or maintains constant is not essential and any profile can be used to achieve the growth oxygen concentration value **C2** between 5 and 100 vol. %. The profiles **1-9** are only exemplary and in practice they might be different, due to diffusion processes, relatively large volume of a crystal growth chamber (hundreds of liters), gas flow rates and gas convection (e.g. due to temperature gradients). Also heating time from room temperature **RT** to the melting temperature **MT** can be appropriately adapted for the crystal growth method and size of a growth furnace. It can be for example between 5 and 30 h.

According to the present invention it is essential that before melting, during melting or just after melting of the Ga_2O_3 starting material the oxygen concentration approaches the growth oxygen concentration value **C2** in the oxygen concentration range **SC** between 5 and 100 vol. % for the reasons explained in connection to Figs. 1A and 1B. Once all the Ga_2O_3 starting material is molten (i.e. at liquid phase), a $\beta\text{-Ga}_2\text{O}_3$ single crystal can be grown from the melt at the growth oxygen concentration value **C2**. The value **C2** can be substantially constant at the growth

temperature **GT** during the whole crystal growth step, as shown by profiles **10** in Figs. 2A and 2B. Alternatively, the growth oxygen concentration value **C2** may decrease to a second growth oxygen concentration value **C2'** at the growth temperature **GT** as shown by the profile **10'** in Fig. 2A. This change always takes place within the oxygen concentration range **SC**. There are several reasons to decrease oxygen concentration during the crystal growth stage: a) upon melting, during seeding and during early stage of the crystal growth step there is a higher decomposition rate of the exposed melt surface as compared with a later stage of the crystal growth step with much smaller exposed melt surface and lower temperature gradients, where smaller oxygen concentration can be used; b) high oxygen concentration (approximately above 25 vol. %) may lead to a high electrical resistivity of the obtained crystals (this is not a problem when semi-insulating or insulating crystals are required); c) lower oxygen concentration will decrease iridium losses. On the other hand, the oxygen concentration may increase at later stage of the crystal growth step from the growth oxygen concentration value **C2** to a third growth oxygen concentration value **C2''** (as shown by the profile **10''** in Fig. 2B) in order to improve the heat transfer through a growing crystal, by lowering the free electron concentration and thus lowering the free carrier absorption in the near infrared spectrum, which becomes more critical with a crystal length. During the crystal growth step both changes can be applied as well. In such case the oxygen concentration **OC** is decreased from the value **C2** to **C2'** at early stage of the crystal growth step and next increased from the value **C2'** to **C2''** at the later stage of the crystal growth step.

It is to be noted that at the liquid-solid interface the melting temperature **MT** and the growth temperature **GT** are the same. However, the **MT** and **GT** are understood in this description in a broader scope. Due to radial temperature gradients within a metal crucible (e.g. the temperature typically decreases from the crucible wall towards the centre), the melt in the crucible is hotter near the crucible wall than in the centre (e.g. by 50 - 100 K). Therefore the **MT** covers all temperatures within the crucible leading to complete melting of the Ga_2O_3 starting material. On the other hand, during the crystal growth step the temperature in the melt changes to remove latent heat of crystallization generated due to liquid-solid phase transition being transported through a growing crystal (not present during melting) and to adapt changes in geometry (a drop of a melt level, an increase of a crystal size etc.) in the way to keep constant temperature at the growth interface. Thus, for the purpose of the present description the **GT** covers all temperature changes in the growth furnace during the crystal growth step.

Time period for the crystal growth step mainly depends on the growth method applied, growth rate, crystal length and like, and may last between about one and hundreds of hours. Once the crystal growth step is completed, the growth furnace together with the crystal is cooled down to room temperature **RT** for a predefined period of time, typically between several and tens of hours, depending on the growth method, furnace and crystal size. During cooling down the oxygen concentration **OC** decreases from the growth oxygen concentration value **C2** to a final oxygen concentration value **C3**, which is typically lower than the growth oxygen concentration value **C2**, **C2'**, **C2''**, as shown in Fig. 2B. Because the crystal has already been grown, the oxygen concentration **OC** at the cooling down step does not need to be changed in such strict manner as during heating up shown in Fig. 2A. The final value **C3** does not need to be very small and may exceed 3 vol. %, for example to tune electrical properties of the obtained crystal. However, it is preferable to achieve a small value to avoid high oxidation of iridium at low temperatures during the cooling down step. The oxygen concentration **OC** can be decreased from the growth oxygen concentration value **C2** to the final oxygen concentration value **C3** in any way, as shown by profiles **11** to **15** or in any combinations thereof. Alternatively, the final oxygen concentration value **C3** may substantially equal to the growth oxygen concentration value **C2**, **C2'**, **C2''**, as shown by the profile **13** in Fig. 2B.

A defined oxygen concentration **OC** at different stages of a growth process is provided to a growth furnace within a growth atmosphere surrounding the melt and crystal. The growth atmosphere is composed of oxygen with variable concentration and one or more of other gasses, including Ar, N₂, He, Xe, Ne, CO₂, CO and traces of H₂ or H₂O, or any combination thereof. Ar, N₂, He, Xe, Ne are neutral gasses, CO₂ is an oxidizing agent, while CO, H₂ and H₂O are reducing agents to additionally modify electrical properties of a β -Ga₂O₃ single crystal. During early heating up and cooling down steps only CO₂ can be used as an oxygen source. Additionally an external overpressure can be used, such as 1-70 bar.

EXAMPLES – GROWTH TECHNIQUES

Now different crystal growth techniques from the melt are exemplary described, which utilize an iridium (or its alloy) crucible and to which the above described invention can be applied to growth β -Ga₂O₃ single crystals or other high melting-point oxides (> 1500°C) requiring a high oxygen concentration, especially those unstable at high temperatures.

Example 1

Fig. 3 schematically shows a growth furnace **100** of the Czochralski method, which is placed within a water-cooled growth chamber (not shown). The growth furnace **100** includes an iridium crucible **101** containing a Ga_2O_3 starting material **102**, which is surrounded by a thermal insulation **103**. The crucible **101** is heated up by a heater **104**, typically an inductive or resistive heater. The heater **104** is connected to a heat generator (not shown) and a controller (not shown). Inside the growth furnace **100** a crystal seed **105** is provided being mounted within a seed holder **106** that is coupled via a pulling rod **107** with a translation and rotation mechanisms (not shown). Inside the growth furnace **100** a growth atmosphere **120** is provided, which is in communication with all furnace parts, including the crucible **101** and the Ga_2O_3 starting material **102**. During the heating up step, the oxygen concentration contained within the growth atmosphere **120** changes from the initial oxygen concentration value **C0** to the intermediate oxygen concentration value **C1** (or alternatively **C1 = C0**) and next approaches the growth oxygen concentration value **C2** around melting of the Ga_2O_3 starting material **102** in the way described in connection to Fig. 2A (or alternatively **C2 = C1**). Once the starting material **102** is molten and stabilized, the crystal seed **105** is brought into a contact with the molten starting material **102** and slowly pulled up with a pulling speed **V** (e.g. between 0.5 – 10 mm/h) while rotating with an angular speed **R** (e.g. at 2 – 30 rpm). By doing so the melt of the Ga_2O_3 starting material **102** solidifies on the crystal seed **105** to form a bulk single crystal **110**. A crystal diameter increases from a seed diameter to a predefined cylinder diameter, which is then kept during the rest of the crystal growth step by regulating melt temperature via the controller. During the crystal growth step the oxygen concentration is maintained at the substantially constant level (profile **10**) of the growth oxygen concentration value **C2**. Alternatively, the growth oxygen concentration value **C2** can be lowered once the predefined cylinder diameter is achieved (profile **10'**). The growth oxygen concentration value **C2** can be also increased at a later stage of the crystal growth step (profile **10''**). Once a predefined crystal length (or mass) is reached, the crystal **110** is separated from the melt and slowly cooled down. During the cooling down step, the oxygen concentration within the growth atmosphere **120** decreases from the growth oxygen concentration **C2** to the final oxygen concentration value **C3** (or alternatively **C3 = C2**) in the way described in connection with Fig. 2B.

Examples 2

Fig. 4 schematically shows a growth furnace **200** of the Kyropoulos method, which is placed within a water-cooled growth chamber (not shown). The Kyropoulos method is a variant of the Czochralski method, where a single crystal **210** is rather growing from a larger surface out

of the melt and partly within a molten starting material **202**. In this method a very small pulling rate **V** (smaller than that in the Czochralski method) is typically applied, possible with rotation **R**. All the components of the growth furnace **200** are very similar to those of the Czochralski method (can be identical). During the heating up step, the oxygen concentration contained within a growth atmosphere **220** changes from the initial oxygen concentration value **C0** to the intermediate oxygen concentration value **C1** (or alternatively **C1 = C0**) and next approaches the growth oxygen concentration value **C2** (or alternatively **C2 = C1**) around melting of the Ga_2O_3 starting material **202** in the way described in connection to Fig. 2A. During the crystal growth stage the oxygen concentration is maintained at the level of the growth oxygen concentration value **C2** or it can be changed during growth within the oxygen concentration range **SC** (e.g. decreased and/or increased). During the cooling down step, the oxygen concentration within the growth atmosphere **220** decreases from the growth oxygen concentration value **C2** to the final oxygen concentration value **C3** (or alternatively **C3 = C2**) in the way described in connection with Fig. 2B.

Examples 3

Fig. 5A schematically shows a growth furnace **300** of the Vertical Bridgman method or the Vertical Gradient Freeze method, which is placed within a water-cooled growth chamber (not shown). The growth furnace **300** includes an iridium crucible **301** containing a Ga_2O_3 starting material **302**, which is surrounded by a thermal insulation **303**. The crucible **301** is enclosed by a lid **308**, preferably of iridium, with an opening **309** through which a growth atmosphere **320** communicates with the Ga_2O_3 starting material **302**. The crucible **301** is heated up by a heater **304** (inductive or resistive). The heater **304** is connected to a heat generator (not shown) and a controller (not shown). At the heating up step, the oxygen concentration contained within the growth atmosphere **320** changes from the initial oxygen concentration value **C0** to the intermediate oxygen concentration value **C1** (or alternatively **C1 = C0**) and next approaches the growth oxygen concentration value **C2** (or alternatively **C2 = C1**) around melting of the Ga_2O_3 starting material **302** in the way described in connection to Fig. 2A. The bottom part of the crucible **301** is tapered and ended with a small diameter tube that functions as a seed holder **306**, within which a crystal seed **305** is accommodated. The iridium crucible **301** is located within vertical temperature gradients in such a way the seed holder **306** along with the crystal seed **305** are held at lower temperature than the rest of the crucible **301** to prevent melting of the seed **305** once all the Ga_2O_3 starting material **302** is molten. The temperature within the crucible **301** typically increases from the seed holder **306** towards the top of the crucible **301**. By lowering the

temperature at the crucible wall (Vertical Gradient Freeze method) the molten Ga_2O_3 starting material **302** slowly solidify on the crystal seed **305** upwards to form a single crystal **310**. Instead of lowering the temperature at the crucible wall, the crucible **301** or the whole growth furnace **300** can be lowered in a direction of lower temperatures (Bridgman method) or the heater **304** is moved in a direction opposite to the crystal seed **305**. Alternatively both lowering the temperature and moving of the crucible **301** / heater **304** can be applied. During the crystal growth step the oxygen concentration is maintained at the level of the growth oxygen concentration value **C2** or it can be changed within the oxygen concentration range **SC**. Once the crystal growth step is completed (i.e. once all the melt is solidified) the growth furnace **300** is cooled down and the oxygen concentration within the growth atmosphere **320** decreases from the growth oxygen concentration value **C2** to the final oxygen concentration value **C3** (or alternatively **C3 = C2**) in the way described in connection with Fig. 2B.

Examples 4

Fig. 5B schematically shows a growth furnace **400** of the Horizontal Bridgman method. The principle of this method is the same as in the case of the Vertical Bridgman method, but the solidification proceeds in a horizontal direction instead of the vertical direction. During the heating up step, the oxygen concentration contained within a growth atmosphere **420** changes from the initial oxygen concentration value **C0** to the intermediate oxygen concentration value **C1** (or alternatively **C1 = C0**) and next approaches the growth oxygen concentration value **C2** (or alternatively **C2 = C1**) around melting of the Ga_2O_3 starting material **402** in the way described in connection to Fig. 2A. During the crystal growth step the oxygen concentration is maintained at the level of the growth oxygen concentration value **C2** or it can be changed during growth within the oxygen concentration range **SC**, while during the cooling down step, the oxygen concentration within the growth atmosphere **420** decreases from the growth oxygen concentration value **C2** to the final oxygen concentration value **C3** (or alternatively **C3 = C2**) in the way described in connection with Fig. 2B.

Example 5

This Example relates to shaped crystal growth techniques in general, such as the Stepanov, Noncapillary Shaping (NCS) and Edge-Defined Film-Fed Growth (EFG) methods. Fig. 6 schematically shows a growth furnace **500** of the EFG method, which is placed within a water-cooled growth chamber (not shown). Within an iridium crucible **501** an iridium die **511** is disposed. The die **511** has at least one opening being in communication with the molten Ga_2O_3

starting material **502** and a small-diameter central channel **512**, through which the melt is transported via capillary forces (capillary channel) to the top surface **513** having typically a quite small width (several millimeters) but much larger length (even several cm). If the central channel **512** is larger than the capillary constant (noncapillary channel), then the melt is transported through the channel by a pressure difference (Stepanov and NCS methods). Once the Ga₂O₃ starting material **502** is molten a crystal seed **505** is brought into the contact with the melt on the top surface **513** and pulled upwards at the pulling speed **V** to form a single crystal **510**. The pulling speed **V** is typically larger than that of the Czochralski method. A crystal rotation is typically not applied in this method. The resulted crystal shape corresponds to the geometry of the top surface **513** which can be different (e.g. rectangular or circular). Once the crystal growth is completed it is separated from the melt and cooled down. During the heating up step, the oxygen concentration contained within a growth atmosphere **520** changes from the initial oxygen concentration value **C0** to the intermediate oxygen concentration value **C1** (or alternatively **C1 = C0**) and next approaches the growth oxygen concentration value **C2** (or alternatively **C2 = C1**) around melting of the Ga₂O₃ starting material **502** in the way described in connection to Fig. 2A. During the crystal growth step the oxygen concentration is maintained at the level of the growth oxygen concentration value **C2** or it can be changed during growth within the oxygen concentration range **SC**, while during the cooling down step, the oxygen concentration within the growth atmosphere **520** decreases from the growth oxygen concentration value **C2** to the final oxygen concentration value **C3** (or alternatively **C3 = C2**) in the way described in connection with Fig. 2B.

Example 6

Fig. 7 schematically shows a growth furnace **600** of the Levitation-Assisted Self-Seeding Crystal Growth Method (LASSCGM), which is placed within a water-cooled growth chamber (not shown). An iridium crucible **601** containing Ga₂O₃ starting material **602** is located within a thermal insulation **603**. The crucible **601** is covered by a lid **608** with an opening **609** for a communication of a growth atmosphere **620** with the Ga₂O₃ starting material **602**. A heater **604** must be an inductive heater in this case. In this method it is required that the Ga₂O₃ starting material is highly conducting in the liquid phase which is then coupled with the electromagnetic field of the inductive heater **604** through the crucible wall and it is levitated. By levitating a portion of the melt a liquid neck **605** is formed, which acts as a seed during solidification. After melting and levitating a portion of the melt, the furnace **600** is cooled down and the molten Ga₂O₃ starting material solidifies on the neck **605** to form two single crystals **610** on the opposite

sides of the self-created neck **605**. More details of the LASSCGM can be found in document WO 2013/159808 to Galazka et al., which is incorporated here by reference. During the heating up step, the oxygen concentration contained within a growth atmosphere **620** changes from the initial oxygen concentration value **C0** to the intermediate oxygen concentration value **C1** (or alternatively **C1 = C0**) and next approaches the growth oxygen concentration value **C2** (or alternatively **C2 = C1**) at or preferably after melting of the Ga_2O_3 starting material **602** in the way described in connection to Fig. 2A. To obtain a high electrical conductivity of the liquid Ga_2O_3 starting material **602** the growth oxygen concentration value **C2** during the crystal growth step should be kept rather at lower level, e.g. 5 – 10 vol. %. Additionally an intentional doping with tetravalent ions (Si, Sn) can be used. During the crystal growth step the oxygen concentration is maintained at the level of the growth oxygen concentration value **C2** (or alternatively **C2 = C1**), while during the cooling down step, the oxygen concentration within the growth atmosphere **620** decreases from the growth oxygen concentration value **C2** to the final oxygen concentration value **C3** (or alternatively **C3 = C2**) in the way described in connection with Fig. 2B.

Example 7

In addition to the above-mentioned techniques, the present invention can also be applied to the micro-pulling down technique. This technique involves a small diameter metal (e.g. iridium) crucible with a small diameter aperture at the bottom part, which prevents the starting material to flow out from the crucible after melting by holding it via capillary forces. Then a seed is brought into a contact with the melt in the aperture and pulled down. In this way a crystal fiber of about 1-2 mm in diameter can be grown. During the heating up step, the oxygen concentration contained within a growth atmosphere changes from the initial oxygen concentration value **C0** to the intermediate oxygen concentration value **C1** (or alternatively **C1 = C0**) and next approaches the growth oxygen concentration value **C2** (or alternatively **C2 = C1**) around melting of the Ga_2O_3 starting material in the way described in connection to Fig. 2A. During the crystal growth step the oxygen concentration is maintained at the level of the growth oxygen concentration value **C2** or it can be changed during the crystal growth step within the oxygen concentration range **SC**, while during the cooling down step, the oxygen concentration within the growth atmosphere **420** decreases from the growth oxygen concentration value **C2** to the final oxygen concentration value **C3** (or alternatively **C3 = C2**) in the way described in connection with Fig. 2B. Due to small crucible dimensions, possible fast heating and fast crystal growth rates, oxygen

concentration can be as high as 100 vol. % during the entire growth process (i.e. $C_0 = C_1 = C_2 = C_3 = 100$ vol. %).

EXAMPLES – OXYGEN CONCENTRATIONS

Example 8 (comparative)

The Czochralski method **100** (Fig. 3, Example 1) was used with an iridium crucible of 40 mm in diameter and height (the amount of the Ga_2O_3 was 1 mole only). The growth atmosphere was CO_2 which provided oxygen concentration at the level of about 1.2 vol. % at the melting temperature **MT**. This means the oxygen concentration was increased from room temperature **RT** to the melting temperature **MT** from substantially 0 vol. % to about 1.2 vol. %, which was then kept constant during the crystal growth step at the growth temperature **GT**. During the cooling down step the oxygen concentration was decreased from 1.2 vol. % at the growth temperature **GT** to about 0 vol. % at room temperature **RT**. The obtained crystal was of 20 mm in diameter and 60 mm in length. The crystal quality was relatively good, although contained crystallographic twins and moderate dislocation density. Moreover, the crystal surface was rough as the result of noticeable Ga_2O_3 decomposition. Due relatively high Ga_2O_3 decomposition the melt was unstable leading to difficulties in seeding and early stage of the crystal growth step. Additionally, some signs of crucible degradation due to eutectic formed between Ga and Ir metals were visible. Similar results were obtained in the case of a growth atmosphere consisting with $O_2 = 2$ vol. % and $N_2 = 98$ vol. %. This example demonstrates that relatively good crystals of β - Ga_2O_3 could be grown with a very low oxygen concentration if the amount of the starting material was very small (1 mole). In reference to Fig. 1A, the amount of metallic Ga produced during Ga_2O_3 decomposition was very small, yet below **CR1** curve, therefore not critical at all. However, first signs of problems associated with growth stability, crystal quality and crucible durability have been recognized.

Example 9 (comparative)

The Czochralski method **100** (Fig. 3, Example 1) was used with much larger iridium crucible of 100 mm in diameter and height. The growth atmosphere was CO_2 , identical to that of Example 8. The only difference was much larger iridium crucible and amount of the Ga_2O_3 starting material by factor of 18 (18 mole of Ga_2O_3). In this case it was almost impossible to start growing a crystal due to a high concentration of metallic Ga being created due to insufficient oxygen concentration in relation to the amount of the Ga_2O_3 starting material. The high

concentration of metallic Ga changes the melt temperature and the melt chemistry. Even the growth could be eventually started, only a short crystal could be obtained (30 mm), although large diameter (50 mm). This was due to high growth instabilities caused by Ga metal. Due to these negative effects the crystal quality was much worse than that of a smaller crystal of Example 8. More importantly, usually after a first growth run the crucible was heavily damaged due to eutectic formed between Ga and Ir metals and could not be reused. Crucible damage and lack of a crystal of a reasonable size and quality lead to high economical losses. This example clearly shows that with increasing amount of the Ga₂O₃ starting material the oxygen concentration must correspondingly increase to obtain: low level of Ga₂O₃ decomposition (i.e. low density of metallic Ga and low evaporation rate), a stable melt flow, much larger crystal size of high structural quality and lower risk of iridium crucible damage.

Example 10

The Czochralski method **100** (Fig. 3, Example 1) was used with an iridium crucible of 100 mm in diameter and height, the same as in Example 9, but a different growth atmosphere was used. During the heating up step, the oxygen concentration was increased from substantially 0 vol. % (the initial oxygen concentration value **C0**) to about 1 vol. % (the intermediate oxygen concentration value **C1**) between room temperature **RT** and the intermediate temperature value **T1** of about 1300°C. This was achieved by using CO₂ only. Then the CO₂ growth atmosphere was replaced with a mixture of Ar = 95 vol. % + O₂ = 5 vol. % as the growth atmosphere at and next with Ar = 92 vol. % + O₂ = 8 vol. % at the beginning of melting of the Ga₂O₃ starting material (the growth oxygen concentration value **C2**), which was kept constant during the rest of the heating up step until complete melting of the Ga₂O₃ starting material (the melting temperature **MT**) and during the entire crystal growth step at the growth temperature **GT**. Once the crystal growth step was completed, the growth atmosphere of Ar (92 vol. %) + O₂ (8 vol. %) was replaced again with CO₂. Oxygen produced during CO₂ decomposition was decreased to 0 – 1 vol. % (the final oxygen concentration value **C3**) at room temperature **RT**. As the result only a very small concentration of metallic Ga was present at the melt surface and it was much easier to start growing a crystal. The obtained crystal was a semiconductor with the free electron concentration of $6 \times 10^{17} \text{ cm}^{-3}$. It was 50 mm in diameter and 125 mm in length, i.e. much longer than that of the comparable Example 9 and of much better structural quality. The crystal was transparent with smooth surface and with no iridium particles therein. Moreover, the iridium crucible has not been damaged by Ga – Ir eutectic and it could be re-used several times.

Example 11

This Example is very similar to that of Example 10 (the Czochralski method **100**, iridium crucible of 100 mm in diameter and height), but a different oxygen concentration was used. The initial oxygen concentration value **C0** was about 0 vol. %, which was increased during the heating up step to about 1.1 vol. % (the intermediate oxygen concentration value **C1**) at about 1700°C (the intermediate temperature value **T1**). This was achieved by using a CO₂ growth atmosphere. Then the oxygen concentration was increased to 12 vol. % (the growth oxygen concentration value **C2**) at the beginning of melting of Ga₂O₃ (the melting temperature **MT**), by replacing the CO₂ growth atmosphere with a mixture of Ar = 88 vol. % + O₂ = 12 vol. % as the growth atmosphere. The growth oxygen concentration value **C2** of 12 vol. % was kept constant during the entire crystal growth step at the growth temperature **GT**. During the cooling down step, the oxygen concentration was decreased to 0 – 1 vol. % (the final oxygen concentration value **C3**) at room temperature **RT**. The metallic Ga concentration was still lower than that in Example 9 and there was quite easy to initiate crystal seeding and growth. The obtained crystal was a semiconductor with the free electron concentration of $2 \times 10^{17} \text{ cm}^{-3}$, which was lower than that in Example 10 due to higher oxygen concentration. The crystal was 50 mm in diameter and 100 mm in length. It was transparent with a very smooth surface. The overall crystal quality was much better as compared with a crystal grown under low oxygen concentration (comparative Example 9). No iridium particles were present inside the crystal and no damage sings of the crucible were visible.

Example 12

This Example is very similar to Examples 10 and 11 (the Czochralski method **100** with 100 mm iridium crucible). The initial oxygen concentration value **C0** was about 0 vol. % which was next increased to the intermediate oxygen concentration value **C1** of about 1 vol. % at about 1500 °C (the intermediate temperature value **T1**), and then to the growth oxygen concentration value **C2** of 20 vol. % just below the melting temperature **MT**. Similar to Example 11, initially CO₂ was used as the growth atmosphere, which was then replaced with a mixture of Ar = 80 vol. % + O₂ = 20 vol. % as the growth atmosphere. The growth oxygen concentration value **C2** of 20 vol. % was kept constant during the entire crystal growth step at the growth temperature **GT**. During the cooling down step, the oxygen concentration was decreased from the growth oxygen concentration value **C2** of 20 vol. % to the final oxygen concentration value **C3** of 0 – 1 vol. % at room temperature **RT**. This was achieved by replacing the Ar + O₂ growth atmosphere with

the CO₂ growth atmosphere during the cooling down step. The obtained crystal was a semiconductor with the free electron concentration of $7 \times 10^{16} \text{ cm}^{-3}$, which was lower than that in Examples 10 and 11 due to yet higher oxygen concentration. The results in terms of the crystal size, appearance and quality, as well as crucible stability were similar to those of Example 10 and 11.

Example 13

This Example is similar to Example 8 (the Czochralski method **100**), but a different growth atmosphere was used. The crucible diameter and height were 40 mm. Additionally the Ga₂O₃ starting material was doped with Mg at a very low level of 0.05 mol. %. The initial oxygen concentration value **C0** at room temperature **RT** was about 0 vol. % which was next increased to the intermediate oxygen concentration value **C1** of about 1 vol. % (by using CO₂) at the intermediate temperature value **T1** of 1460 °C, and then to the growth oxygen concentration value **C2** of 35 vol. % by using a mixture of N₂ = 65 vol. % + O₂ = 35 vol. % as the growth atmosphere at temperature below the melting temperature **MT**, which was then kept constant during the entire crystal growth step at the growth temperature **GT**. Oxygen concentration changes during the heating up step were step-wise (oxygen was increased in steps of about 5 vol. % in temperature intervals of about 50 - 100 K by changing a N₂/O₂ ratio). During the cooling down step, the oxygen concentration was decreased from the growth oxygen concentration value **C2** of 35 vol. % at growth temperature **GT** to the final oxygen concentration value **C3** of about 1 vol. % at room temperature **RT** in the step-wise manner by changing the N₂/O₂ ratio. The obtained crystal of 20 mm in diameter and 60 mm in length was an electrical insulator. The structural quality of the crystal was as good as that in Examples 10-12.

Example 14

This Example is similar to the Example 13 (the Czochralski method **100**), but a different growth atmosphere was used. The crucible diameter and height were 40 mm. The initial oxygen concentration value **C0** at room temperature **RT** was 3 vol. % (a mixture of Ar = 97 vol. % + O₂ = 3 vol. %) which was kept constant as the intermediate oxygen concentration value **C1** (**C1** = **C0**) until the intermediate temperature value **T1** of 1820 °C which is equal to the melting temperature **MT** (**T1** = **MT**), that is when the all Ga₂O₃ starting material was in the liquid phase. Next the oxygen concentration at the melting temperature **MT** was abruptly increased from the intermediate oxygen concentration value **C1** to the growth oxygen concentration value **C2** of 12.5 vol. % by an increase of the O₂ flow with respect to the Ar flow. The growth oxygen

concentration value **C2** was kept constant at the growth temperature **GT** during seeding, growth of the crystal shoulder and the beginning of the crystal cylinder. Next the growth oxygen concentration value **C2** was decreased (as shown by the profile **10'** in fig. 2A) to a second growth oxygen concentration value **C2'** of 9.7 vol. % (**C2' < C2**), which was kept constant during growth of most of the crystal cylinder. When the crystal cylinder achieved of about 2/3 of the final length, the second growth oxygen concentration value **C2'** was increased (as shown by the profile **10''** in fig. 2B) to a third growth oxygen concentration value **C2''** of 13.8 vol. % (**C2'' > C2**). During the cooling down step, just after the crystal growth step was completed, the growth atmosphere consisting of Ar+O₂ was replaced with CO₂, and the final oxygen concentration value **C3** was 0 – 1 vol. % at room temperature **RT**. The obtained crystal 20 mm in diameter and 60 mm in length was a semiconductor with the free electron concentration of $6 \times 10^{17} \text{ cm}^{-3}$. Other features were very similar to those in previous Examples 10 - 13.

Example 15

In this Example the Kyropoulos method **200** was utilized, as schematically shown in Fig. 4. The iridium crucible diameter and height were 40 mm. The initial oxygen concentration value **C0** was about 0 vol. % at room temperature **RT**, which was next increased to the intermediate oxygen concentration value **C1** of about 1.1 % (from CO₂) at the intermediate temperature value **T1** of 1630 °C, and then to the growth oxygen concentration value **C2** of 16 vol. % just below the melting temperature **MT**. This was obtained by replacing CO₂ with a mixture of N₂ = 84 vol. % + O₂ = 16 vol. %. The growth oxygen concentration value **C2** of 16 vol. % was kept constant during the initial stage of crystal growth at the growth temperature **GT**. Once the initial stage of crystal growth was completed (seeding and crystal shoulder), the growth oxygen concentration value **C2** of 16 vol. % was decreased to a second oxygen concentration value **C2'** of 8 %, which was kept constant to the end of the crystal growth step at the growth temperature **GT**. The final oxygen concentration value **C3** at room temperature **RT** was 3 vol. %, obtained by a decrease (from the growth oxygen concentration value **C2** in a step-wise manner) of the O₂ flow in relation to the N₂ flow. The resulted crystal was of 32 mm in diameter and 20 mm in length. Similar to the above-described Examples 9 - 14, the obtained crystal was a transparent semiconductor with the free electron concentration of $1 \times 10^{17} \text{ cm}^{-3}$ and high structural quality. No signs of a crucible damage were observed.

Example 16

In this example the Vertical Bridgman or VGF method **300** was utilized as schematically shown in Fig. 5A. The cylindrical part of the crucible was of 60 mm and 80 mm in diameter and length, respectively. The bottom conical part of the crucible of 25 mm in length was ended with a 5 mm tube acting as a seed holder. In this experiment Sn (0.1 mol % of SnO₂ in the Ga₂O₃ starting material) was used as an intentional dopant to obtain high electrical conductivity of the obtained crystal despite of a very high oxygen concentration. The initial oxygen concentration value **C0** was 0 vol. % at room temperature **RT**, which was then increased to the intermediate oxygen concentration value **C1** of about 1 vol. % (from the CO₂ growth atmosphere) at the intermediate temperature value **T1** of 1430 °C. During the next stage of the heating up step the intermediate oxygen concentration value **C1** of 1 vol. % was increased to the growth oxygen concentration value **C2** of 17 vol. % (by replacing CO₂ with a mixture of N₂ = 83 vol. % + O₂ = 17 vol %) below the melting temperature **MT**. The value **C2** of 17 vol. % was kept constant during melting and during the crystal growth step at the growth temperature **GT**. Once the crystal growth step was completed and after an initial stage of the cooling down step, the growth oxygen concentration value **C2** was decreased during the next stage of the cooling down step to the final oxygen concentration value **C3** of about 0 – 1 vol. % (by replacing N₂ + O₂ with CO₂) at room temperature **RT**. The obtained crystal was 50 mm in diameter and 35 mm long. It was a transparent semiconductor with the free electron concentration of $5 \times 10^{18} \text{ cm}^{-3}$. No signs of crucible damage was observed.

Example 17

In this example two shaped crystal growth techniques were used: the NCS and EFG methods **500**, as schematically shown in Fig. 6. The cylindrical iridium crucible diameter and height were 40 mm. The die was made of iridium and had a conically-shaped circular top surface of 16 mm to obtain a cylindrical crystal of the same diameter. The central channel **512** was of 12 mm in diameter in the case of the NCS variant and 1 mm in diameter in the case of the EFG variant. The initial oxygen concentration value **C0** was about 0 % at room temperature **RT**, which was next increased to the intermediate oxygen concentration value **C1** of 1 % (from CO₂) at the intermediate temperature value **T1** of 1400 °C, and then to the growth oxygen concentration value **C2** of 12 % just below the melting temperature **MT**. This was obtained by replacing CO₂ with a mixture of Ar = 88 vol. % + O₂ = 12 vol. %. The growth oxygen concentration value **C2** of 12 % was kept constant during the entire crystal growth step at the growth temperature **GT**. The final oxygen concentration value **C3** at room temperature **RT** was about 0 - 1 vol. %, obtained by replacing N₂ + O₂ with CO₂. The resulted single crystals were

semiconductors of 16 mm in diameter and 50 mm in length. No iridium crucible and die damage was observed.

Example 18

In this example the Levitation-Assisted Self-Seeding Crystal Growth Method **600** was utilized as schematically shown in Fig 7. The iridium crucible was of 40 mm in diameter and height. To obtain a very high electrical conductivity of Ga₂O₃ in the liquid phase an intentional doping with Sn (0.2 mol % of SnO₂ in the Ga₂O₃ starting material) was used. The initial oxygen concentration value **C0** was 2 vol. % at room temperature **RT**, which was kept constant to the intermediate temperature value **T1** of 1500 °C, that is **C1 = C0**. Next, the intermediate oxygen concentration value **C1** of 2 vol. % (a mixture of N₂ = 98 vol. % + O₂ = 2 vol. %) was increased to the growth oxygen concentration value **C2** of 5 vol. % (by an increase of the O₂ flow with respect to the N₂ flow) below the melting temperature **MT**. The value **C2** of 5 vol. % was kept constant during melting and during the crystal growth step at the growth temperature **GT**. Once the crystal growth step was completed and after the initial stage of the cooling down step, the growth oxygen concentration value **C2** was decreased during the next stage of the cooling down step to the final oxygen concentration value **C3** of about 1 vol. % (by a decrease of the O₂ flow with respect to the N₂ flow) at room temperature **RT**. The obtained crystal was 35 mm in diameter and 20 mm long with relatively good structural quality. It was a transparent semiconductor with the free electron concentration of $1 \times 10^{19} \text{ cm}^{-3}$. No signs of a crucible damage was observed.

The growth atmosphere in addition to main constituents (O₂, CO₂, N₂, Ar) and depending on a growth process contained also other gases, such as H₂O between 0 - 1.5 vol. %, H₂ between 0 - 0.1 vol. %, CO between 0 – 2 vol. % (mainly from CO₂ decomposition) and He between 0 - 100 vol. ppm. Typically the growth atmosphere contained several gases, especially in the case of replacing one atmosphere with another one.

Using the growth atmosphere according to the teaching of the present invention significantly decreases eutectic formation between solid iridium crucible and metallic gallium formed during decomposition of Ga₂O₃. This is of particular importance when using large growth systems to obtain large single crystals of several kg by weight (e.g. cylindrical crystals of 2-4 inch in diameter grown by the Czochralski method), what is required at the industrial level. At the same time also evaporation of volatile species of Ga₂O₃ have been minimized or eliminated. Secondly, the obtained crystals, whether small or large, were of high structural

quality when using the inventive growth atmosphere. The full width of half maximum (FWHM) of the rocking curve (determining structural quality) was around or below 50 arcsec when using the novel growth atmosphere indicating an improvement by factor of two or three when compared with crystals grown at low oxygen concentration (around 100-150 arcsec). Furthermore, the crystals obtained under the novel growth atmosphere had lower dislocation density (not exceeding several thousand per cm^2) by factor of 10-100 as compared with the crystals grown with use of the atmosphere containing lower oxygen concentration. Moreover, the inventive growth atmosphere minimized or even eliminated crystallographic twinning, cleaving and cracking. Also the crystal surface became smooth and shiny as the decomposition of Ga_2O_3 was significantly reduced. In additions to much improved crystal quality, high oxygen concentration at liquid Ga_2O_3 contained within a metal crucible allowed for much easier seeding and more stable crystal growth process. A combination of the above-mentioned advantages of the present inventions led to a high overall production yield of the crystals (a combination of crystal size and quality as well as extended life of an iridium crucible). Yet another advantage of the present invention is the possibility of modifying electrical and optical properties of the crystals by using different oxygen concentrations during the growth and/or cooling down steps. For example, crystals grown at very high oxygen concentrations (> 25 vol %) may turn into semi-insulating or insulating state, while at lower values of the oxygen concentration the crystals remain semiconducting. Therefore depending on needs the crystals can be grown either as insulators, semi-insulators or semiconductors, with yet different electrical properties.

Unexpectedly and surprisingly, the obtained crystals did not contain any iridium particles, in contrast to low oxygen concentrations, when iridium particles are often present in the obtained crystals. This is due to very high iridium oxide partial pressure at high temperatures, which evaporates very effectively just after creation. If high oxygen concentration is used at moderate temperatures (600 – 1000°C), then iridium oxide partial pressure is very low and may simply contaminate the starting material contacting the iridium crucible. Despite of extremely high oxygen concentration according to the present invention (up to 100 vol. %) at high temperatures iridium losses due to oxidation and evaporation are quite low and acceptable, between 2 - 9 wt. % per growth run depending on oxygen concentration and duration of the growth run. In the case of 100 vol. % of oxygen, 9 wt. % of iridium loss relates to one-day growth run, while at lower oxygen concentrations several wt. % of iridium loss relates to several-day growth runs.

The present invention can be applied for obtaining β -Ga₂O₃ single crystals which are either undoped or intentionally doped with a number of elements to further modify (if needed), in addition to oxygen concentration, electrical and optical properties of the crystals. Some of the crystals described in reference to Examples 10-18 were undoped, while other ones were doped either with divalent ions (Mg) to obtain insulating crystals or tetravalent ions (Sn) to increase the electrical conductivity of the crystals despite of high oxygen concentration. In connection to the inventive growth atmosphere any dopants can be used, as required.

The crystal growth atmosphere according to the present invention has a very broad spectrum of applications, as it can be applied to any crystal growth method utilizing a metal crucible comprising iridium or its alloys. These methods have been described in connection with Examples 1-18 and Figs. 3-7. Any modifications or adaptations of these methods are also encompassed, as long as a metal crucible is used at high temperatures (> 1500°C).

High structural quality of the obtained β -Ga₂O₃ crystals allows for fabrication of high quality wafers or substrates for depositing thereon homo- or heteroepitaxial films or layers with use of various epitaxial techniques. Homoepitaxial films or layers may include β -Ga₂O₃ single crystal films of different conductivity than the substrate, while heteroepitaxial films involve other compounds, such as different oxides or nitrides (GaN, AlN, AlGa_N, InN, InGa_N and like). The epitaxial techniques include, but not limited to Molecular Beam Epitaxy (MBE), Metal-Organic Chemical Vapor Deposition (MOCVD), Pulsed Laser deposition (PLD), Sputtering, Electron Beam Evaporation and like. Wafers or substrates prepared from β -Ga₂O₃ single crystals can also be used as seeds for other growth techniques, such as, but not limited to Chemical Vapor Transport (CVT), Physical Vapor Transport (PVT) and like.

β -Ga₂O₃ single crystals according to the present invention can be used in a diversity of applications, such as, but not limited to: light emitting diodes, solid-state lasers, transparent or high power field-effect transistors (such as MISFET and MOSFET), Schottky diodes and high temperature gas sensors (electrical properties change on oxidizing and reducing conditions at elevated temperatures).

The essence of the present invention is the use of a very high oxygen concentration (5 - 100 vol. %) in connection with an iridium crucible (or its alloys) at high temperatures (> 1500°C). This is a general finding, which can be applied to any oxide crystals grown from the melt contained within the iridium crucible and which require high oxygen concentrations. In particular the present invention is suitable for other transparent conducting or semiconducting oxides, which are thermally unstable and require high oxygen partial pressure or concentration.

Examples of such oxides include, but not limited to ZnO, In₂O₃, NiO, SnO₂, BaSnO₃, their compounds and like. The inventive growth atmosphere is also suitable for other groups of electronic and optical oxide single crystals, such as, but not limited to: scintillators, laser materials (including second harmonic generation), piezoelectrics etc.

It is important to note that the operating conditions, arrangement and design of the methods as shown in the various embodiments are illustrative only. Although only exemplary embodiments of the present invention have been described in detail in this disclosure, those skilled in the art will readily appreciate that many modifications are possible, e.g., variations in values of crystal growth parameters, crystal growth atmosphere compositions, use of materials, use of crystal growth techniques, process designs etc. without materially departing from the novel teachings and advantages of the subject matter recited in the claims. Accordingly, all such modifications are intended to be included within the scope of the present invention as defined in the appended claims. Other substitutions, modifications, changes and omissions may be made in the operating conditions and arrangement of the preferred and other exemplary embodiments without departing from the scope of the present inventions.

Reference numeral list

1 - 9	Oxygen concentration profiles vs. temperature during heating up step
10, 10', 10''	Oxygen concentration profiles during crystal growth step
11-15	Oxygen concentration profiles vs. temperature during cooling down step
100, 200, 300, 400, 500, 600	Crystal growth furnace
101, 201, 301, 401, 501, 601	Metal crucible
102, 202, 302, 402, 502, 602	Ga ₂ O ₃ starting material
103, 203, 303, 403, 503, 603	Thermal insulation
104, 204, 304, 404, 504, 604	Heater
105, 205, 305, 405, 505, 605	Crystal seed
106, 206, 306, 406, 506	Seed holder
107, 207, 507	Pulling rod
110, 210, 310, 410, 510, 610	Single crystal
120, 220, 320, 420, 520, 620	Growth atmosphere
308, 408, 608	Lid covering the crucible 301, 401, 601
309, 409, 609	Opening in the lid 308, 408, 608
511	Die of the metal crucible 501
512	Central channel of the die 511
513	Top surface of the die 511
OC	Oxygen concentration
C0, C1, C2, C2', C2'', C3	Oxygen concentration values: initial, intermediate, growth and final
T1	Intermediate temperature value
ST	Range of temperature values T1
SC	Range of oxygen concentrations at the growth temperature
MT	Melting temperature
GT	Growth temperature
RT	Room temperature
V	Pulling speed
R	Rotation rate

Claims

1. A method for growing beta phase of gallium oxide (β -Ga₂O₃) single crystals from the melt contained within a metal crucible, comprising the steps of:

- providing into a growth chamber a thermal system or growth furnace (100, 200, 300, 400, 500, 600) comprising the metal crucible (101, 201, 301, 401, 501, 601) containing the Ga₂O₃ starting material (102, 202, 302, 402, 502, 602), a thermal insulation (103, 203, 303, 403, 503, 603) surrounding the metal crucible (101, 201, 301, 401, 501, 601) and a heater (104, 204, 304, 404, 504, 604) disposed around the metal crucible (101, 201, 301, 401, 501, 601);
- providing or creating a crystal seed (105, 205, 305, 405, 505, 605) within the growth furnace (100, 200, 300, 400, 500, 600);
- introducing at least into the growth furnace (100, 200, 300, 400, 500, 600) a growth atmosphere (120, 220, 320, 420, 520, 620) containing oxygen;
- heating up the metal crucible (101, 201, 301, 401, 501, 601) by the heater (104, 204, 304, 404, 504, 604), which in turns heats up the Ga₂O₃ starting material (102, 202, 302, 402, 502, 602) until melting;
- contacting the crystal seed (105, 205, 305, 405, 505, 605) with the molten Ga₂O₃ starting material (102, 202, 302, 402, 502, 602) contained within the metal crucible (101, 201, 301, 401, 501, 601);
- growing a β -Ga₂O₃ single crystal (110, 210, 310, 410, 510, 610) on the crystal seed (105, 205, 305, 405, 505, 605) by temperature gradients between the crystal seed and the melt;
- cooling down the grown β -Ga₂O₃ single crystal (110, 210, 310, 410, 510, 610) to room temperature (RT) once the crystal growth step has been completed;

characterized in that it further comprises the steps of:

- i) providing into the growth furnace (100, 200, 300, 400, 500, 600) the growth atmosphere (120, 220, 320, 420, 520, 620) with a variable oxygen concentration (OC) or partial pressure in such a way that the oxygen concentration (OC) reaches a growth oxygen concentration value (C₂, C₂', C₂'') in the concentration range (SC) of 5 – 100 vol. % below (8, 9) the melting temperature (MT) of Ga₂O₃ or at (6, 7) the melting temperature (MP) or after (5) complete melting of the Ga₂O₃ starting material (102, 202, 302, 402, 502, 602) adapted to minimize creation of metallic gallium amount

(**CR1, CR2, CR3**) and thus eutectic formation with the metal crucible (**101, 201, 301, 401, 501, 601**) and to improve stoichiometry of the Ga_2O_3 starting material (**102, 202, 302, 402, 502, 602**) and crystal growth stability; and

ii) maintaining the growth oxygen concentration value (**C2, C2', C2''**) within the oxygen concentration range (**SC**) during the crystal growth step of the $\beta\text{-Ga}_2\text{O}_3$ single crystal (**110, 210, 310, 410, 510, 610**) from the melt at the growth temperature (**GT**).

2. The method according to claim 1, wherein the oxygen concentration (**OC**):

iii) does not exceed an intermediate oxygen concentration value (**C1**) in the range of 0 - 5 vol. % during the heating up step from room temperature (**RT**) to an intermediate temperature value (**T1**), intermediate temperature value (**T1**) being located within the temperature range (**ST**) between 1000°C and the melting temperature (**MT**) of Ga_2O_3 ;

iv) increases from the intermediate oxygen concentration value (**C1**) to the growth oxygen concentration value (**C2, C2', C2''**) in the oxygen concentration range (**SC**) of 5 – 100 vol. % during the heating up step from the intermediate temperature value (**T1**) to the melting temperature (**MT**) of Ga_2O_3 or at the melting temperature (**MT**) or after complete melting of the Ga_2O_3 starting material (**102, 202, 302, 402, 502, 602**) if the intermediate temperature value (**T1**) substantially equals to the melting temperature (**MT**).

3. The method according to claim 1 or 2, wherein the oxygen concentration (**OC**):

v) decreases from the growth oxygen concentration value (**C2, C2', C2''**) to a final oxygen concentration value (**C3**) being lower than the growth oxygen concentration value (**C2, C2', C2''**) during the cooling down step from the growth temperature (**GT**) to room temperature (**RT**).

4. The method according to claim 1, wherein the growth oxygen concentration value (**C2**) is substantially constant (**10**) within the oxygen concentration range (**SC**) at the growth temperature (**GT**) during the entire crystal growth step.

5. The method according to claim 1, wherein the growth oxygen concentration value (**C2**) decreases (**10'**) to a second growth oxygen concentration value (**C2'**) within the oxygen concentration range (**SC**) at the growth temperature (**GT**) after an early stage of the crystal growth step.

6. The method according to claim 1, wherein the growth oxygen concentration value (C2) increases (10'') to a third growth oxygen concentration value (C2'') within the oxygen concentration range (SC) at the growth temperature (GT) at the later stage of the crystal growth step.
7. The method according to claim 1, wherein the growth oxygen concentration value (C2) first decreases (10') to a second growth oxygen concentration value (C2') within the oxygen concentration range (SC) at the growth temperature (GT) after an early stage of the crystal growth step, and increases (10'') to a third growth oxygen concentration value (C2'') within the oxygen concentration range (SC) at the growth temperature (GT) at the later stage of the crystal growth step.
8. The method according to claim 1, wherein the growth atmosphere (120, 220, 320, 420, 520, 620) contains in addition to oxygen at least one of the gases selected from the group consisting of Ar, N₂, He, CO₂, CO, H₂ and H₂O or any combination thereof.
9. The method according to any one of the preceding claim 1-8, wherein the growth atmosphere (120) is applied to the Czochralski method (100).
10. The method according to any one of the preceding claim 1-8, wherein the growth atmosphere (220) is applied to the Kyropoulos method (200).
11. The method according to any one of the preceding claim 1-8, wherein the growth atmosphere (320) is applied to the vertical Bridgman or Vertical Gradient Freeze method (300).
12. The method according to any one of the preceding claim 1-8, wherein the growth atmosphere (420) is applied to the horizontal Bridgman method (400).
13. The method according to any one of the preceding claim 1-8, wherein the growth atmosphere (520) is applied to shaped crystal growth techniques selected from the group consisting of the Stepanov, Noncapillary Shaping and Edge-Defined Film-Fed Growth methods (500).
14. The method according to any one of the preceding claim 1-8, wherein the growth atmosphere (620) is applied to the Levitation Assisted Self-Seeding Crystal Growth method (600).

15. The method according to any one of the preceding claim 1-8, wherein the growth atmosphere is applied to the Micro-Pulling Down method.

16. A bulk β -Ga₂O₃ single crystal (110, 210, 310, 410, 510, 610), wherein it is obtained from the melt of the Ga₂O₃ starting material (102, 202, 302, 402, 502, 602) contained within a metal crucible (101, 201, 301, 401, 501, 601) according to any one of the preceding claims 1 – 15.

17. A use of the bulk β -Ga₂O₃ single crystal (110, 210, 310, 410, 510, 610) according to claim 16, wherein it is fabricated into a wafers or substrates for epitaxial films or layers.

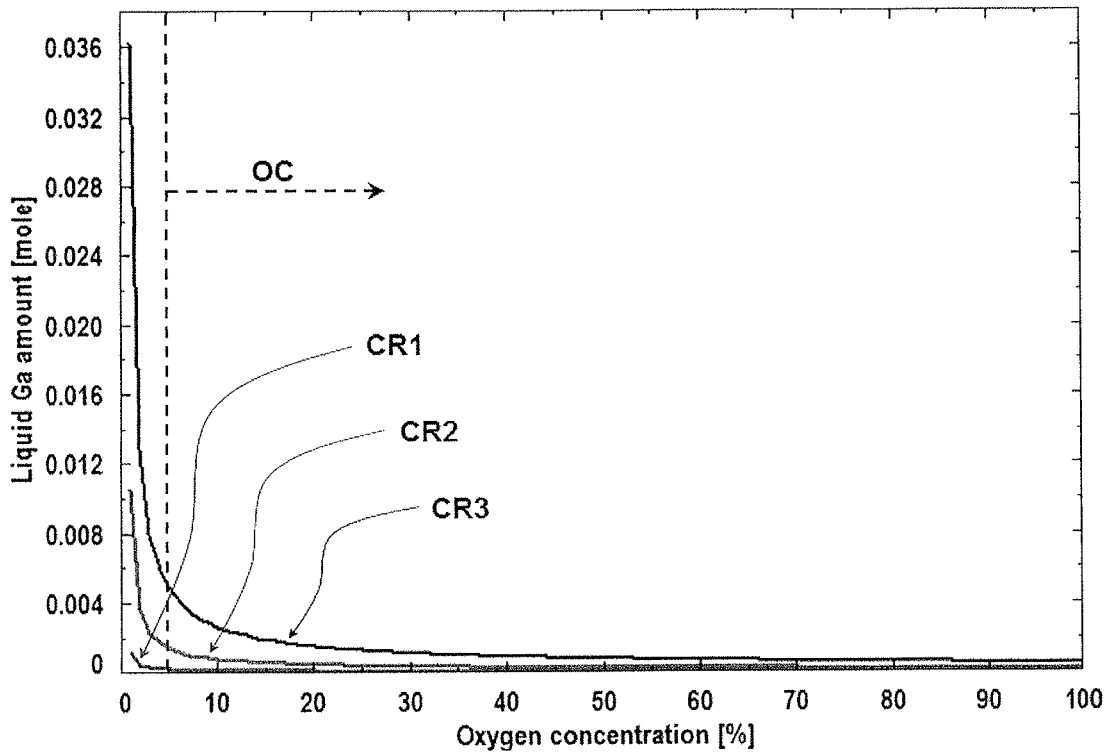


Fig. 1A

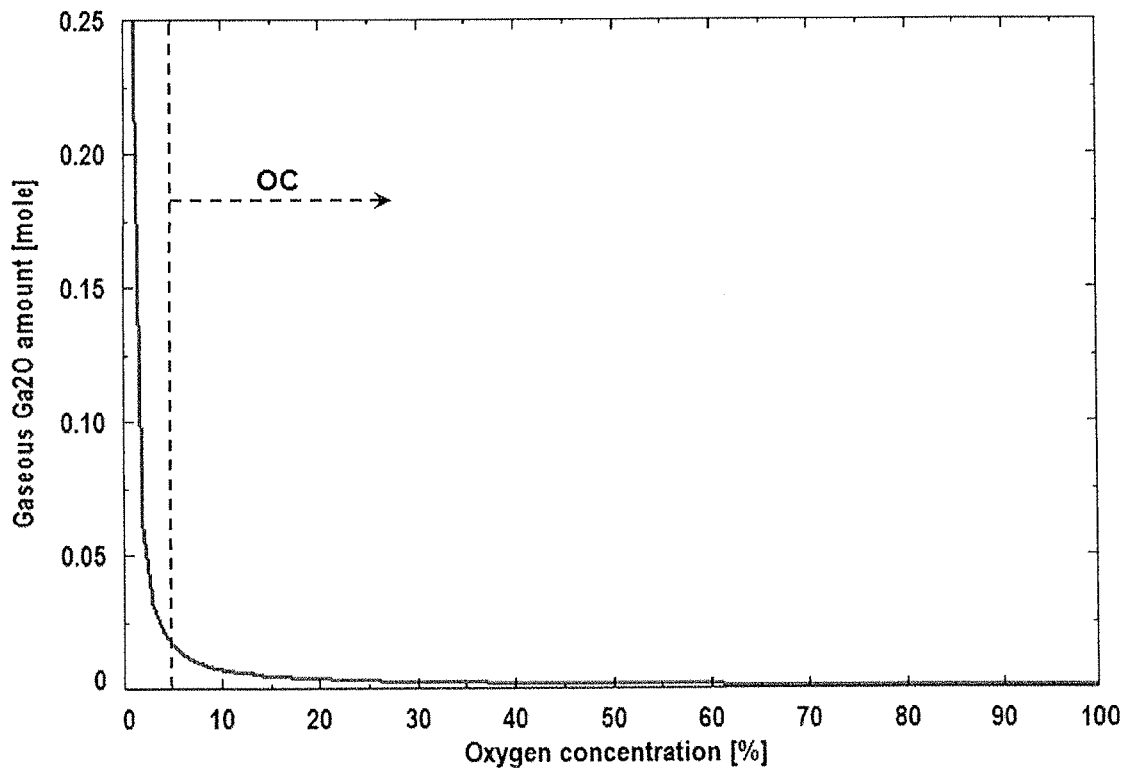


Fig. 1B

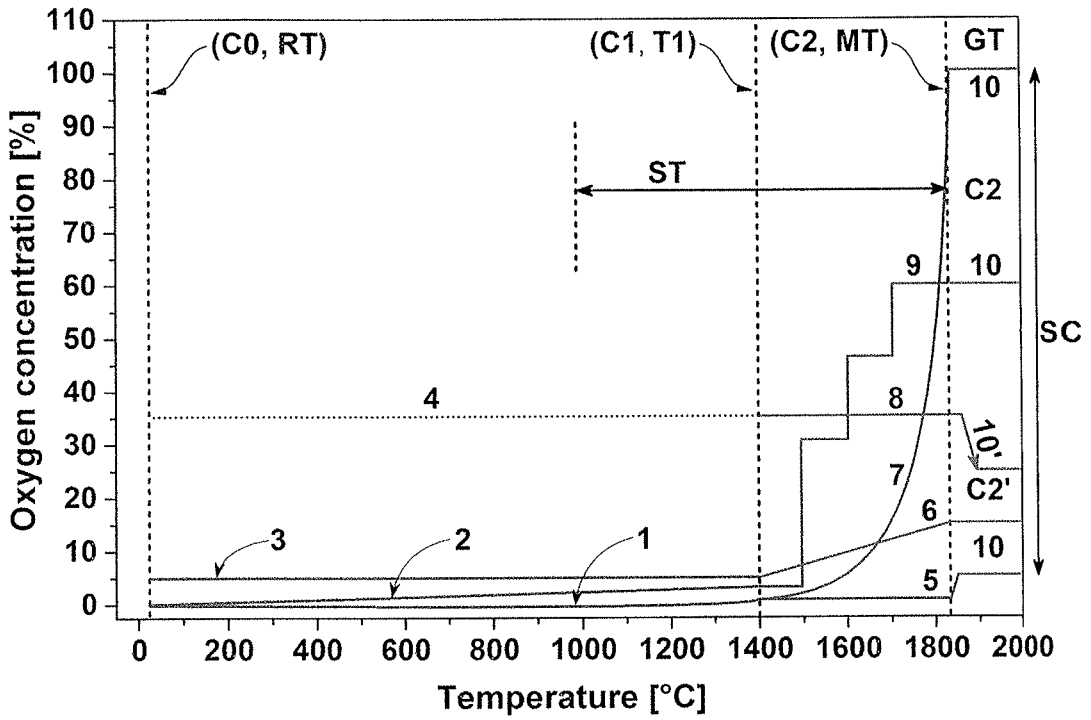


Fig. 2A

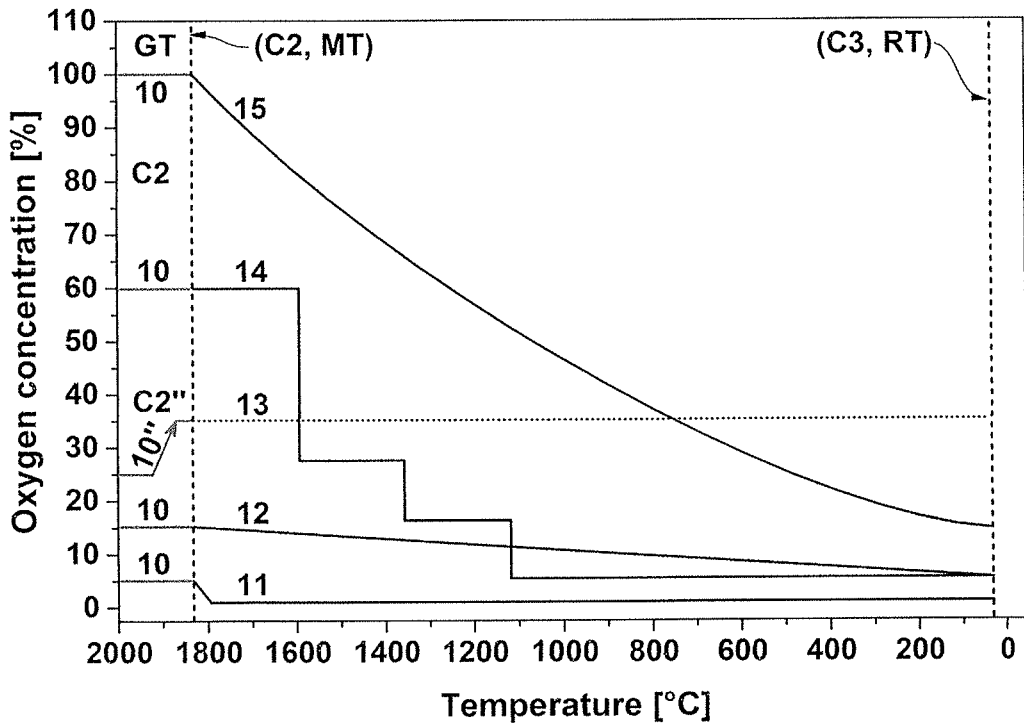


Fig. 2B

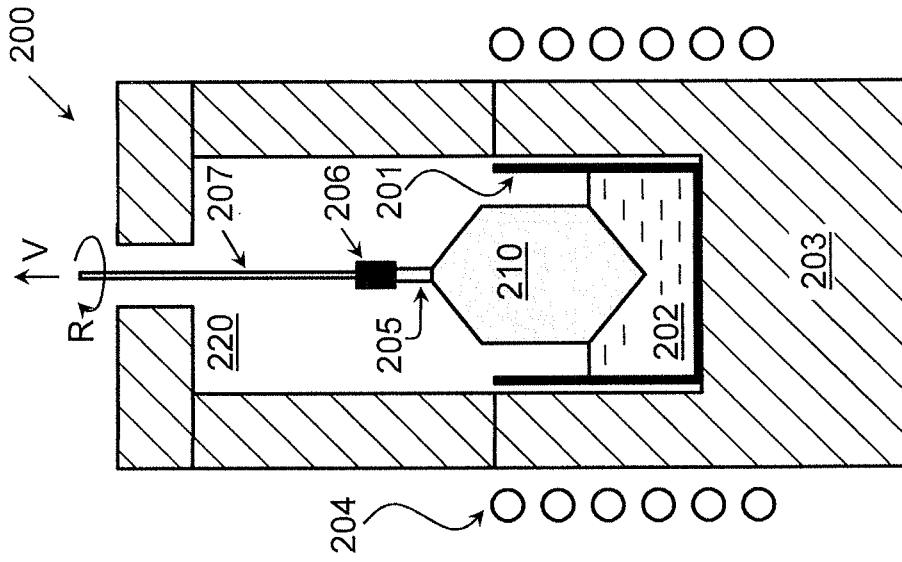


Fig. 4

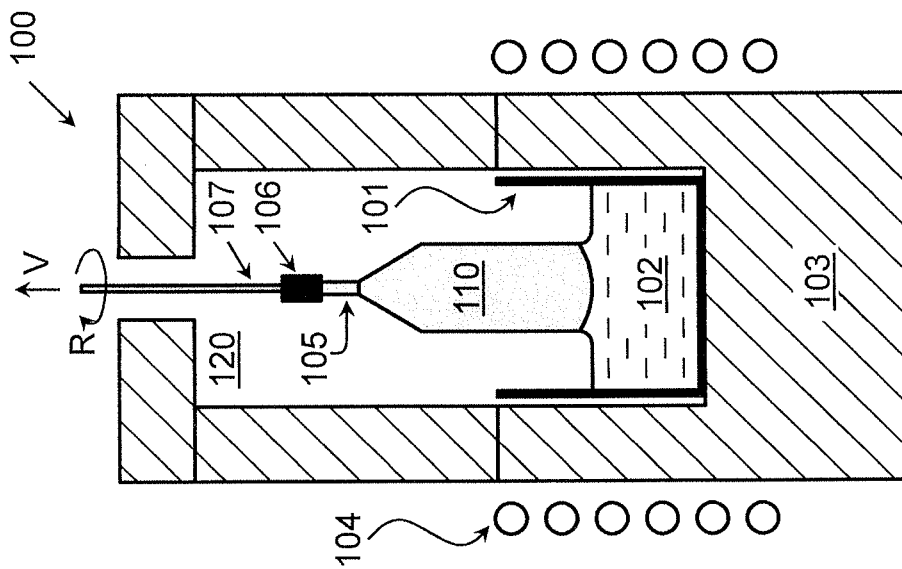


Fig. 3

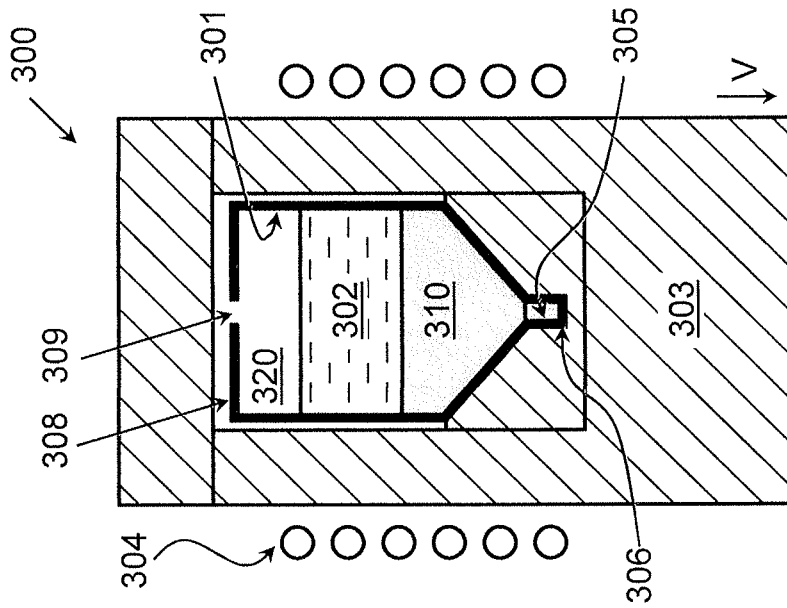


Fig. 5A

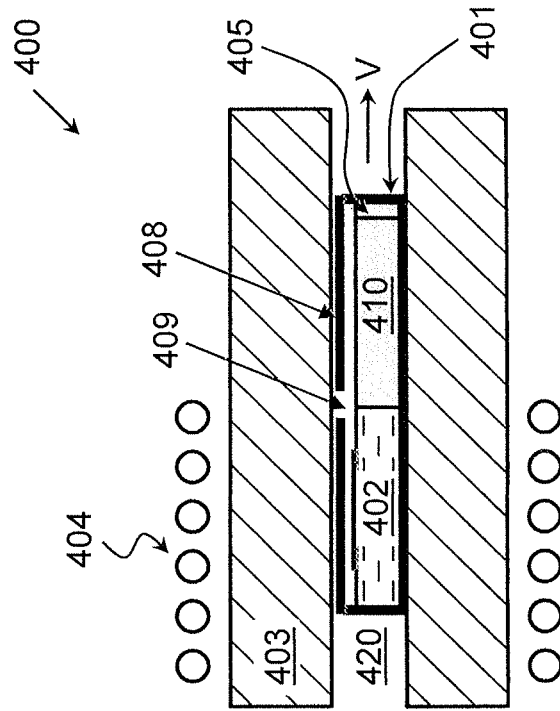


Fig. 5B

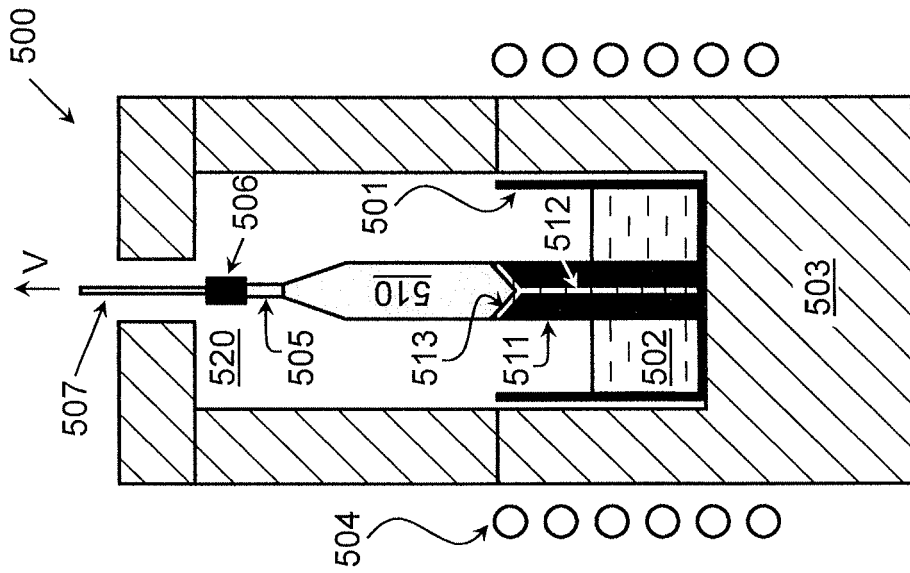


Fig. 6

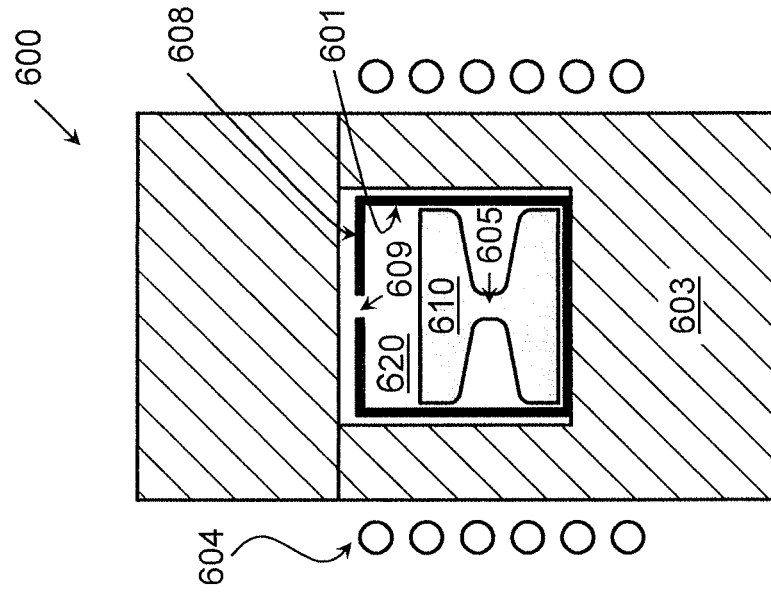


Fig. 7

INTERNATIONAL SEARCH REPORT

International application No
PCT/EP2015/079938

A. CLASSIFICATION OF SUBJECT MATTER
 INV. C30B29/16 C30B15/20 C30B17/00 C30B11/00
 ADD.
 According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED
 Minimum documentation searched (classification system followed by classification symbols)
 C30B

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)
 EPO-Internal

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	VÍLLORA ENCARNACIÓN ET AL: "Epitaxial relationship between wurtzite GaN and[β]-Ga ₂ O ₃ ", APPLIED PHYSICS LETTERS, AMERICAN INSTITUTE OF PHYSICS, US, vol. 90, no. 23, 4 June 2007 (2007-06-04), pages 234102-234102, XP012095205, ISSN: 0003-6951, DOI: 10.1063/1.2745645 page 1, column 1 - column 2 ----- -/--	16,17

Further documents are listed in the continuation of Box C.

See patent family annex.

* Special categories of cited documents :

- "A" document defining the general state of the art which is not considered to be of particular relevance
- "E" earlier application or patent but published on or after the international filing date
- "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)
- "O" document referring to an oral disclosure, use, exhibition or other means
- "P" document published prior to the international filing date but later than the priority date claimed

- "T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention
- "X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone
- "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art
- "&" document member of the same patent family

Date of the actual completion of the international search 9 February 2016	Date of mailing of the international search report 16/02/2016
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Name and mailing address of the ISA/ European Patent Office, P.B. 5818 Patentlaan 2 NL - 2280 HV Rijswijk Tel. (+31-70) 340-2040, Fax: (+31-70) 340-3016	Authorized officer Aliouane, Nadir
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INTERNATIONAL SEARCH REPORT

International application No
PCT/EP2015/079938

C(Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	ZBIGNIEW GALAZKA ET AL: "On the bulk [beta]-Ga203 single crystals grown by the Czochralski method", JOURNAL OF CRYSTAL GROWTH, vol. 404, 1 October 2014 (2014-10-01), pages 184-191, XP055166284, ISSN: 0022-0248, DOI: 10.1016/j.jcrysgr.2014.07.021	16,17
Y	page 184, column 1 page 185, column 1 - page 186, column 2; figure 5 page 187, column 2 page 188, columns 1-2 page 190, columns 1-2	1-15
Y	----- Morteza Asadian: "The Influence of Atmosphere on Oxides Crystal Growth" In: "Modern Aspects of Bulk Crystal and Thin Film Preparation", 13 January 2012 (2012-01-13), InTech, XP055166135, ISBN: 978-9-53-307610-2 DOI: 10.5772/29648, whole document; figures 2-6; compound 3	1-15
A	----- ASADIAN M ET AL: "Improvement of Nd:GGG crystal growth process under dynamic atmosphere composition", SOLID STATE SCIENCES, vol. 14, no. 2, 13 January 2012 (2012-01-13), pages 262-268, XP028885176, ISSN: 1293-2558, DOI: 10.1016/J.SOLIDSTATESCIENCES.2011.11.030 abstract; figures 2,3,4 pages 263-265 page 262, column 1, paragraph 2 - column 2, paragraph 2	1-15
A	----- TOMM Y ET AL: "Czochralski grown Ga203 crystals", JOURNAL OF CRYSTAL GROWTH, ELSEVIER, AMSTERDAM, NL, vol. 220, no. 4, 1 December 2000 (2000-12-01), pages 510-514, XP004225848, ISSN: 0022-0248, DOI: 10.1016/S0022-0248(00)00851-4 whole document	1-16
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INTERNATIONAL SEARCH REPORT

International application No
PCT/EP2015/079938

C(Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	<p>Z. GALAZKA ET AL: "Czochralski growth and characterization of [beta]-Ga203 single crystals", CRYSTAL RESEARCH AND TECHNOLOGY, vol. 45, no. 12, 26 August 2010 (2010-08-26), pages 1229-1236, XP055166291, ISSN: 0232-1300, DOI: 10.1002/crat.201000341 page 1229 - page 1230; figures 1,5 -----</p>	1-17